GTM

CORPORATION

ISSUED DATE :2005/08/01 REVISED DATE :2006/05/23B

GESBL1630CT~1660CT

SCHOTTKY BARRIER RECTIFIERS

REVERSE VOLTAGE 30V TO 60V, CURRENT 16A

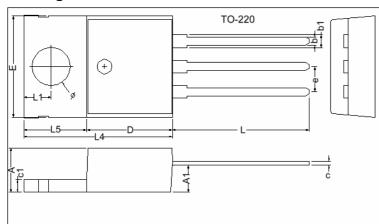
Description

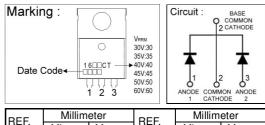
The GESBL1630CT~1660CT are designed for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

Features

- Guard ring for transient protection
- Low power loss, high efficiency
- High current capability, low VF
- · High surge capacity

Package Dimensions





	REF.	Millimeter		REF.	Millimeter		
		Min.	Max.	IILI.	Min.	Max.	
	Α	4.40	4.80	c1	1.25	1.45	
	b	0.76	1.00	b1	1.17	1.47	
	С	0.36	0.50	L	13.25	14.25	
	D	8.60	9.00	е	2.54 REF.		
	Е	9.80	10.4	L1	2.60	2.89	
	L4	14.7	15.3	Ø	3.71	3.96	
	L5	6.20	6.60	A1	2.60	2.80	

Maximum Ratings and Electrical Characteristics at Ta=25℃ unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%

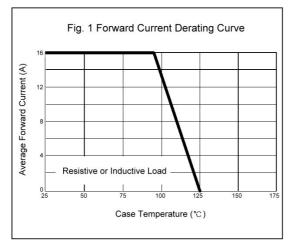
I I I I I I I I I I I I I I I I I I I	Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%									
Parameters	Symbol	Ratings						Unit		
Farameters		GESBL 1630CT	GESBL 1635CT	GESBL 1640CT	GESBL 1645CT	GESBL 1650CT	GESBL 1660CT	V		
Max. Recurrent Peak Reverse Voltage	V_{RRM}	30	35	40	45	50	60	V		
Max. RMS Voltage	V_{RMS}	21	24.5	28	31.5	35	42	V		
Max. DC Blocking Voltage	V_{DC}	30	35	40	45	50	60	V		
Max. Average Forward @T _c =95°C Rectified Current (See Fig.1)	$I_{(AV)}$	16					Α			
Peak Surge Forward Current 8.3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I _{FSM}	250						Α		
Max. Forward Voltage @ 8A (Note 1)	V_{F}	0.55 0.7					.7	٧		
Max. DC Reverse Current @T _J =25℃ At Rated DC Blocking Voltage @T _J =100℃	I_R	0.5 50						mA		
Typical Thermal Resistance (Note 2)	$R_{ heta JC}$	2.5						°C/W		
Operating Temperature Range	Tj	-55 ~ +125						$^{\circ}\!\mathbb{C}$		
Storage Temperature Range	Tstg	-55 ~ +150						$^{\circ}\!\mathbb{C}$		

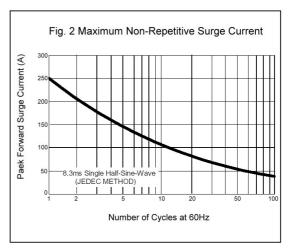
Notes: 1. 300us Pulse Width, 2% Duty Cycle.

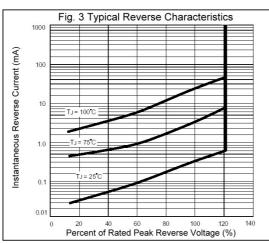
2. Thermal Resistance Junction to Case.

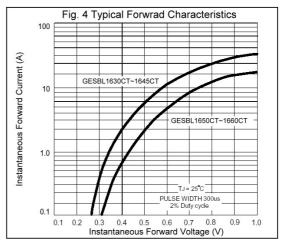
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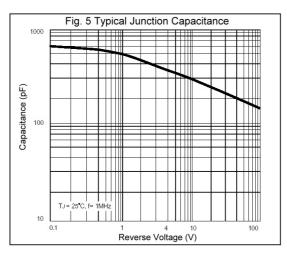
Characteristics Curve











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 Head Office And Factory:
 Taiwan: No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
 TEL: 886-3-597-7061 FAX: 886-3-597-9220, 597-0785
 China: (201203) No.255, Jang-Jiang Tsai-Lueng RD., Pu-Dung-Hsin District, Shang-Hai City, China
 TEL: 86-21-5895-7671 ~ 4 FAX: 86-21-38950165

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